

IN THE SPECIFICATION:

Please amend paragraph [0001] as follows:

[0001] This application is a continuation of application Serial No. 09/843,119, filed April 26, 2001, ~~pending~~, now U.S. Patent 6,634,100, issued October 21, 2003, which is a divisional of application Serial No. 09/533,407, filed March 23, 2000, now U.S. Patent 6,529,027, issued March 4, 2003.

Please amend paragraph [0004] as follows:

[0004] Tests are typically performed at several stages of ~~manufacture~~, manufacture for the purposes of evaluating the electrical characteristics of various circuits of the semiconductor devices and for detecting electrical, structural, and other types of faults in the semiconductor devices. These tests are sometimes performed on representative semiconductor ~~devices~~, devices and sometimes on each semiconductor device of a certain type, depending on the criticality of use, manufacturing costs, and expectation of flaws.

Please amend paragraph [0073] as follows:

[0073] In practicing the present invention, a commercially available stereolithography apparatus operating generally in the manner as that described with respect to apparatus 10 of FIG. 9 is preferably employed. For example and not by way of limitation, the SLA-250/50HR, SLA-5000 and SLA-7000 stereolithography systems, each offered by 3D Systems, Inc. of Valencia, California, are suitable for modification. Photopolymers believed to be suitable for use in practicing the present invention include Cibatool SL 5170 and SL 5210 resins for the SLA-250/50HR system, Cibatool SL 5530 resin for the SLA-5000 and Cibatool SL 7510 resin for the SLA-7000 system. All of these resins are available from Ciba Specialty Chemicals ~~Company~~, Inc. By way of example and not limitation, the layer thickness of material 16 to be formed, for purposes of the invention, may be on the order of 0.001 to 0.002 inch, with a high degree of uniformity over a field on a surface 30 of a platform 20. It should be noted that different material layers may be of different heights, so as to form a structure of a precise, intended total height or to provide different material thicknesses for different portions of a

structure. The size of the laser beam "spot" impinging on the surface of liquid material 16 to cure same may be on the order of 0.002 inch to 0.008 inch. Resolution is preferably \pm 0.0003 inch in the X-Y plane (parallel to surface 30) over at least a 0.5 inch X 0.25 inch field from a center point, permitting a high resolution scan effectively across a 1.0 inch X 0.5 inch area. Of course, it is desirable to have substantially this high a resolution across the entirety of surface 30 of platform 20 to be scanned by laser beam 28, which area may be termed the "field of exposure," such area being substantially coextensive with the vision field of a machine vision system employed in the apparatus of the invention as explained in more detail below. The longer and more effectively vertical the path of laser beam 26/28, the greater the achievable resolution.

Please amend paragraph [0080] as follows:

[0080] The material 16 selected for use in forming the interposer 100 may be a photopolymer such as one of the above-referenced resins from Ciba Specialty-Chemical Company Chemicals Inc. which are believed to exhibit a desirable dielectric constant and low shrinkage upon cure, are of sufficient (i.e., semiconductor grade) purity, exhibit good adherence to other materials used in semiconductor devices, and have a coefficient of thermal expansion (CTE) sufficiently similar to that of the interposer substrate 110 so that the substrate and the fence 120 are not stressed during thermal cycling in testing and use. One area of particular concern in determining resin suitability is the substantial absence of mobile ions and, specifically, fluorides.